

Supplementary Information

A near-infrared photodetector based on carbon nanotube transistors exhibits ultra-low dark current through field-modulated charge carrier transport

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Figure S1. Dark current of QD heterojunction photodetectors

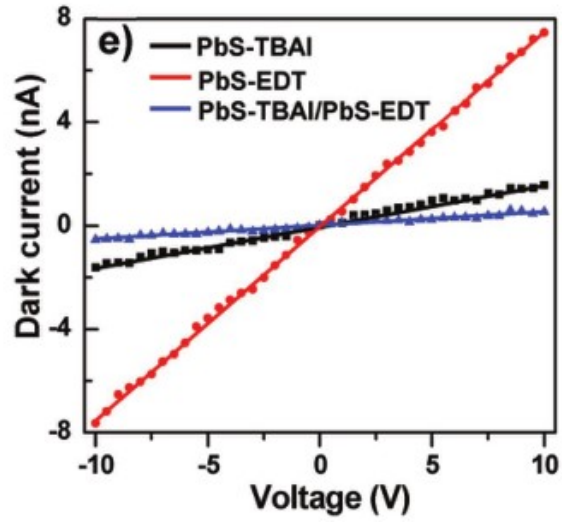


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